Abstracts

2.0 W CW X-Band GaInP/GaAs Heterojunction Bipolar Transistor

W. Liu, T. Kim and A. Khatizbadeh. "2.0 W CW X-Band GaInP/GaAs Heterojunction Bipolar Transistor." 1994 Microwave and Guided Wave Letters 4.1 (Jan. 1994 [MGWL]): 14-16.

We report 2.0 W CW (continuous wave) output power at 9.5 GHz with a GaInP/GaAs HBT having a total emitter area of 2 x 500 μm². The collector-emitter bias dependence and the frequency dependence of the large-signal performance of both the 2 x 400 and 2 x 500 μm² unit cells are described. The uniformity of the output power and power-added efficiency is also discussed.

❑ Return to main document.

Click on title for a complete paper.